NSN 5962-01-226-2270

Memory Microcircuit - Page 1 of 2



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Body Length:	
0.840 inches	
Body Width:	
Between 0.220 inches and	0.310 inches
Body Height:	
0.185 inches	
Maximum Power Dissipa	ion Rating:
739.0 milliwatts	
Operating Tempurature F	ange:
-55.0/+125.0 degrees cels	JS
Storage Tempurature Ra	ıge:
-65.0/+150.0 degrees cels	JS
End Application:	
An/bps14to15e	
Features Provided:	
Hermetically sealed and be	rn in and bipolar and schottky and programmable and w/active pull-up
Inclosure Material:	
Ceramic	
Inclosure Configuration:	
Dual-in-line	
Output Logic Form:	
Transistor-transistor logic	
Input Circuit Pattern:	
10 input	
Case Outline Source And	Designator:
D-2 mil-m-38510	
Terminal Surface Treatm	ent:
Solder	
Voltage Rating And Type	Per Characteristic:
7.0 volts power source	
Time Rating Per Chacter	stic:
75.00 nanoseconds propa	gation delay time, low to high level output and 75.00 nanoseconds propagation delay time, high to low level
output	
Memory Device Type:	
Rom	
Memory Capacity:	
Unknown	
Test Data Document:	
96906-mil-std-883 standar	l (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quan	ity:
16 printed circuit	
Shelf Life:	
N/a	

NSN 5962-01-226-2270

Memory Microcircuit - Page 2 of 2

Unit Of Measure:

Demilitarization:

Yes - demil/mli

Fiig:

A458a0

